AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) An electrical component ~~with a piezoelectric functional layer,~~ comprising

[[-]] a substrate; ~~(S)~~

[[-]] a first electrode layer; ~~(E1)~~

[[-]] a ~~structured~~ growth layer ~~(W)~~ that is ~~thin relative to said~~ structured and that is thinner than the first electrode layer;

[[-]] a piezoelectric layer; and ~~(P)~~

[[-]] a second electrode layer ~~(E2)~~.

2. (Currently Amended) The electrical component ~~in accordance with~~ of claim 1, ~~in which said~~ wherein the growth layer ~~(W)~~ is ~~applied to said~~ on the first electrode layer ~~(E1)~~, the growth layer is structured relative to ~~said~~ the first electrode layer, and the growth layer has a smaller surface area than the first electrode layer ~~latter~~.

3. (Currently Amended) The electrical component ~~in accordance with~~ of claim 1 ~~or 2~~, ~~in which said~~ wherein the piezoelectric layer ~~(P) completely~~ (i) substantially covers ~~said~~ the growth layer ~~(W),~~ and (ii) overlaps the ~~latter~~ growth layer along a perimeter of

the growth layer, thereby causing ~~its entire circumference, and encloses there with said~~ the piezoelectric layer and the first electrode layer to substantially enclose the growth layer ~~(E1)~~.

4. (Currently Amended) The electrical component of claim 1 ~~in accordance with any of claims 1 – 3, in which said~~ wherein the growth layer ~~(W) is selected depending on said piezoelectric layer (P) such that it supports its~~ supports ordered growth relative to the piezoelectric layer.

5. (Currently Amended) The electrical component of claim 1 ~~in accordance with any of claims 1 – 4, in which said~~ wherein the growth layer ~~(W) is selected from~~ comprises at least one of the following: Au, Mo, W, Pt, Si_3N_4, sapphire, spinel, Si, Ba_3TiO_3, ZrO_2, MgO, and TiO_2.

6. (Currently Amended) The electrical component of claim 1 ~~in accordance with any of claims 1 – 5~~, wherein the ~~in which said~~ piezoelectric layer comprises at least one of ~~(P) is selected from~~ AlN and ZnO.

7. (Currently Amended) The electrical component of claim 1 ~~in accordance with any of claims 1 – 6, in which said~~ wherein the first electrode layer ~~(E1) has a multilayer structure that includes~~ comprises multiple layers, the multiple layers comprising a titanium layer and another layer that is not titanium ~~as a different layer from the upper~~

~~most layer of the multilayer structure~~.

8. (Currently Amended) The electrical component of claim 1 ~~in accordance with any of claims 1 – 7, in which~~ further comprising:

an acoustic mirror ~~(AS) is arranged~~ between the substrate ~~(S)~~ and the first electrode layer ~~(E1)~~.

9. (Currently Amended) The electrical component of claim 1 ~~in accordance with any of claims 1 – 7~~, further comprising:

~~including~~ a multilayer structure ~~with~~ comprising a plurality of piezoelectric layers; and ~~(P),~~

~~between each of which is arranged~~ an additional electrode layer ~~(E)~~ and an additional growth layer between pairs of the plurality of piezoelectric layers ~~(W)~~.

10. (Currently Amended) ~~Component in accordance with claim 9, embodied as~~ A piezoelectric actuator comprising the electrical component of claim 1.

11. (Currently Amended) ~~Component in accordance with any of claims 1 – 8, embodied as an arrangement with~~ A bulk acoustic wave resonator comprising:

the electrical component of claim 1 ~~at least one resonator working with bulk acoustic waves~~.

12. (Currently Amended) A method ~~for~~ of producing a component that includes ~~that includes~~ at least one bulk acoustic wave resonator, the method comprising: ~~working with bulk acoustic waves, with the steps~~

[[-]] applying a first electrode layer ~~(E1)~~ to a substrate; ~~(S)~~

[[-]] structuring ~~said~~ the first electrode layer ~~at least~~ to produce a first electrode region; ~~(E11)~~

[[-]] applying a growth layer ~~(W) over said~~ to the first electrode region; ~~(E11)~~

[[-]] structuring ~~said~~ the growth layer ~~such~~ to produce ~~that~~ a growth region ~~remains exclusively~~ over ~~said~~ the first electrode region, the growth region having ~~and has~~ a smaller surface area than ~~said~~ the first electrode region; ~~(E11)~~

[[-]] ~~whole-surface growth of~~ growing a piezoelectric layer ~~(P) under conditions that make possible a~~ having crystal-axis oriented growth over ~~said~~ the growth region;

[[-]] structuring ~~of said~~ the piezoelectric layer ~~(P) such~~ so that ~~it~~ the piezoelectric layer completely covers ~~said~~ the growth region[[,]] and so that the piezoelectric layer overlaps ~~it~~ the growth region ~~laterally~~ along a perimeter of the growth region ~~its entire circumference~~, ~~and encloses there with said~~ wherein the first electrode layer and the piezoelectric layer enclose the growth region; ~~(E1)~~

[[-]] ~~application~~ applying ~~and structuring of~~ a second electrode layer above the piezoelectric layer relative to the first electrode layer; and ~~(E2)~~

structuring the second electrode layer.

13. (Currently Amended) The method ~~in accordance with~~ of claim 12 ~~9~~,

wherein ~~in which the~~ structuring ~~of said~~ the growth layer ~~(W) occurs~~ is performed via wet chemical etching ~~wet chemically~~.

14. (Currently Amended) The method of claim 12 ~~in accordance with claim 9 or 10~~, wherein applying the growth layer comprises vapor-depositing ~~in which~~ a gold layer ~~is vapor-deposited as said growth layer (W)~~.

15. (Currently Amended) The method of claim 12 ~~in accordance with any of claims 9 – 12~~, wherein growing the ~~in which the growth of said~~ piezoelectric layer ~~(P) occurs by means of~~ is performed via a CVD or PVD process.

16. (New) The electrical component of claim 2, wherein the piezoelectric layer (i) substantially covers the growth layer and (ii) overlaps the growth layer along a perimeter of the growth layer, thereby causing the piezoelectric layer and the first electrode layer to substantially enclose the growth layer.

17. (New) The electrical component of claim 2, wherein the growth layer supports ordered growth relative to the piezoelectric layer.

18. (New) The electrical component of claim 2, wherein the growth layer comprises at least one of the following: Au, Mo, W, Pt, Si_3N_4, sapphire, spinel, Si, Ba_3TiO_3, ZrO_2, MgO, and TiO_2.

19. (New) The electrical component of claim 2, wherein the piezoelectric layer comprises at least one of AlN and ZnO.

20. (New) The electrical component of claim 2, wherein the first electrode layer comprises multiple layers, the multiple layers comprising a titanium layer and another layer that is not titanium.